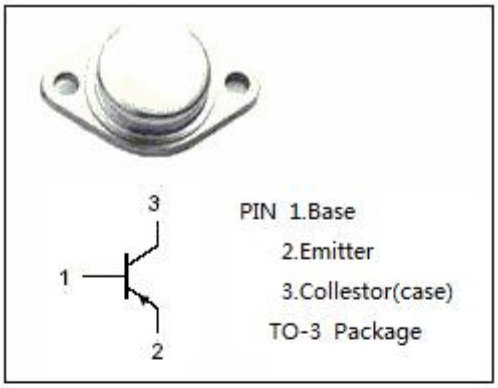
isc Silicon NPN Power Transistor 2N6275



DESCRIPTION

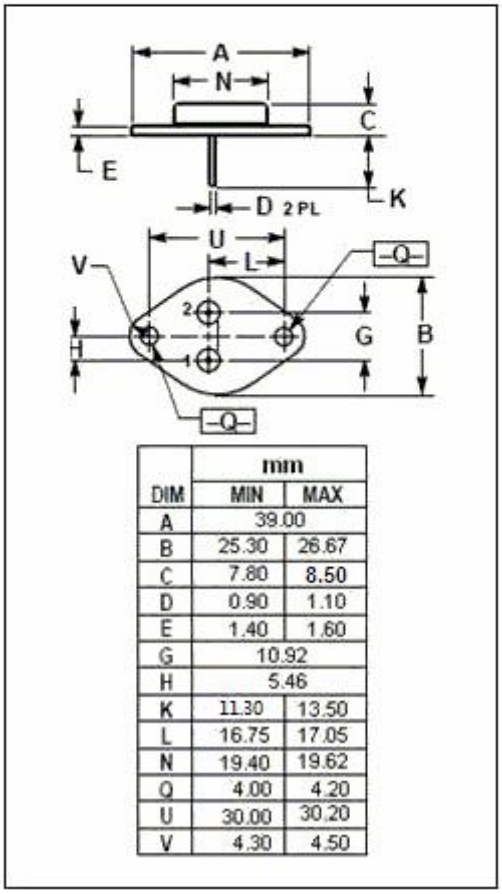
- Collector-Emitter Breakdown Voltage-
  : V_{CEO}=120V(Min)
- Minimum Lot-to-Lot variations for robust device Performance and reliable operation

APPLICATIONS

- Power amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	140	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	50	A
P_D	Collector Power Dissipation @ T_C=25℃	250	W
T_J	Junction Temperature	-65~200	℃
T_{stg}	Storage Temperature Range	-65~200	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	Ic=50mA	120			V
I_{EBO}	Emitter-Base Cutoff Current	V_{BE}=6V			100	uA
I_{CEO}	Collector-Emitter Cutoff Current	V_{CE}= 60V			50	uA
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C=20A; I_B= 2A			1	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 50A; I_B= 10A			3	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= 20A; I_B= 2A			1.8	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C=50A; I_B= 10A			3.5	V
h_{FE-1}	DC Current Gain	I_C=1A; V_{CE}= 4V	50			
h_{FE-2}	DC Current Gain	I_C=20A; V_{CE}=4V	30		120	
h_{FE-3}	DC Current Gain	I_C=50A; V_{CE}= 4V	10			